

## N-Channel 60 V (D-S) MOSFET



### FEATURES

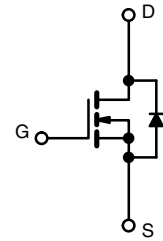
- TrenchFET® Gen IV power MOSFET
- Very low  $R_{DS(on)}$  -  $Q_g$  figure-of-merit (FOM)
- Tuned for the lowest  $R_{DS(on)}$  -  $Q_{oss}$  FOM
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Synchronous rectification
- Primary side switch
- DC/DC converter
- Solar micro inverter
- Motor drive switch
- Battery and load switch
- Industrial



N-Channel MOSFET

### PRODUCT SUMMARY

|  |         |
|--|---------|
| $V_{DS}$ (V)                                       | 60      |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V  | 0.00175 |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5$ V | 0.00240 |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 6$ V   | 0.00340 |
| $Q_g$ typ. (nC)                                    | 42.5    |
| $I_D$ (A)  | 165     |
| Configuration                                      | Single  |

### ORDERING INFORMATION

|                                 |                  |
|---------------------------------|------------------|
| Package                         | PowerPAK SO-8    |
| Lead (Pb)-free and halogen-free | SiR626ADP-T1-RE3 |

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

| PARAMETER   | SYMBOL         | LIMIT         | UNIT                 |                     |
|---|----------------|---------------|----------------------|---------------------|
| Drain-source voltage                                      | $V_{DS}$       | 60            | V                    |                     |
| Gate-source voltage                                       | $V_{GS}$       | $\pm 20$      |                      |                     |
| Continuous drain current ( $T_J = 150$ °C)                | $I_D$          | $T_C = 25$ °C | 165                  |                     |
|   |                | $T_C = 70$ °C | 132                  |                     |
|   |                | $T_A = 25$ °C | 40.4 <sup>b, c</sup> |                     |
|   |                | $T_A = 70$ °C | 32.4 <sup>b, c</sup> |                     |
| Pulsed drain current ( $t = 100$ $\mu$ s)                 | $I_{DM}$       | 300           | A                    |                     |
| Continuous source-drain diode current                     | $I_S$          | $T_C = 25$ °C |                      | 100 <sup>a</sup>    |
|   |                | $T_A = 25$ °C |                      | 5.6 <sup>b, c</sup> |
| Single pulse avalanche current                            | $I_{AS}$       | 50            |                      | mJ                  |
| Single pulse avalanche energy                             | $E_{AS}$       | 125           |                      |                     |
| Maximum power dissipation                                 | $P_D$          | $T_C = 25$ °C | 104                  |                     |
|   |                | $T_C = 70$ °C | 66.6                 |                     |
|   |                | $T_A = 25$ °C | 6.25 <sup>b, c</sup> |                     |
|   |                | $T_A = 70$ °C | 4 <sup>b, c</sup>    |                     |
| Operating junction and storage temperature range          | $T_J, T_{stg}$ | -55 to +150   | °C                   |                     |
| Soldering recommendations (peak temperature) <sup>c</sup> |                | 260           |                      |                     |

#### Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s



| THERMAL RESISTANCE RATINGS               |              |                   |         |         |      |  |
|--|--------------|-------------------|---------|---------|------|--|
| PARAMETER                                |              | SYMBOL            | TYPICAL | MAXIMUM | UNIT |  |
| Maximum junction-to-ambient <sup>a</sup> | t ≤ 10 s     | R <sub>thJA</sub> | 15      | 20      | °C/W |  |
| Maximum junction-to-case (drain)         | Steady state | R <sub>thJC</sub> | 0.9     | 1.2     |      |  |

**Notes**

a. Surface mounted on 1" x 1" FR4 board

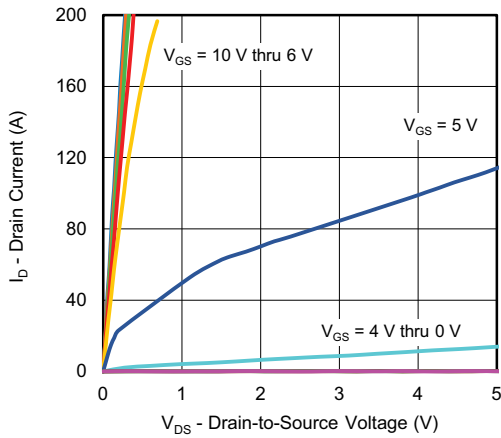
| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                                      |  |   |         |         |       |     |
|---|--------------------------------------|--|---|---------|---------|-------|-----|
| PARAMETER   | SYMBOL                               | TEST CONDITIONS  | MIN.  | TYP.    | MAX.    | UNIT  |     |
| <b>Static</b>   |                                      |  |   |         |         |       |     |
| Drain-source breakdown voltage                                  | V <sub>DS</sub>                      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA   | 60  | -       | -       | V     |     |
| V <sub>DS</sub> temperature coefficient                         | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = 1 mA  | -   | 32      | -       | mV/°C |     |
| V <sub>GS(th)</sub> temperature coefficient                     | ΔV <sub>GS(th)</sub> /T <sub>J</sub> | I <sub>D</sub> = 250 μA  | -   | -7.8    | -       | mV/°C |     |
| Gate-source threshold voltage                                   | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA  | 2   | -       | 3.5     | V     |     |
| Gate-source leakage   | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V  | -   | -       | 100     | nA    |     |
| Zero gate voltage drain current                                 | I <sub>DSS</sub>                     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V  | -   | -       | 1       | μA    |     |
|   |                                      | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C  | -   | -       | 15      |       |     |
| On-state drain current <sup>a</sup>                             | I <sub>D(on)</sub>                   | V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V   | 40  | -       | -       | A     |     |
| Drain-source on-state resistance <sup>a</sup>                   | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A  | -   | 0.00145 | 0.00175 | Ω     |     |
|   |                                      | V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 20 A   | -   | 0.00190 | 0.00240 |       |     |
|   |                                      | V <sub>GS</sub> = 6 V, I <sub>D</sub> = 20 A   | -   | 0.00260 | 0.00340 |       |     |
| Forward transconductance <sup>a</sup>                           | g <sub>fs</sub>                      | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A  | -   | 84      | -       | S     |     |
| <b>Dynamic <sup>b</sup></b>                                     |                                      |  |   |         |         |       |     |
| Input capacitance   | C <sub>iss</sub>                     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz   | -   | 3770    | -       | pF    |     |
| Output capacitance  | C <sub>oss</sub>                     |  | -   | 1370    | -       |       |     |
| Reverse transfer capacitance                                    | C <sub>rss</sub>                     |  | -   | 40      | -       |       |     |
| Total gate charge   | Q <sub>g</sub>                       | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A  | -   | 55      | 83      | nC    |     |
| Gate-source charge  | Q <sub>gs</sub>                      | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 20 A   | -   | 42.5    | 64      |       |     |
| Gate-drain charge   | Q <sub>gd</sub>                      |  | -   | 16.7    | -       |       |     |
| Output charge   | Q <sub>oss</sub>                     |  | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V | -       | 88.5    |       | -   |
| Gate resistance   | R <sub>g</sub>                       |  | f = 1 MHz                                     | 0.3     | 0.9     |       | 1.6 |
| Turn-on delay time  | t <sub>d(on)</sub>                   | V <sub>DD</sub> = 30 V, R <sub>L</sub> = 1.5 Ω, I <sub>D</sub> ≅ 20 A,<br>V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω  | -   | 16      | 32      | ns    |     |
| Rise time   | t <sub>r</sub>                       |  | -   | 10      | 20      |       |     |
| Turn-off delay time   | t <sub>d(off)</sub>                  |  | -   | 30      | 60      |       |     |
| Fall time   | t <sub>f</sub>                       |  | -   | 10      | 20      |       |     |
| Turn-on delay time  | t <sub>d(on)</sub>                   | V <sub>DD</sub> = 30 V, R <sub>L</sub> = 1.5 Ω, I <sub>D</sub> ≅ 20 A,<br>V <sub>GEN</sub> = 7.5 V, R <sub>g</sub> = 1 Ω | -   | 20      | 40      |       |     |
| Rise time   | t <sub>r</sub>                       |  | -   | 20      | 40      |       |     |
| Turn-off delay time   | t <sub>d(off)</sub>                  |  | -   | 27      | 54      |       |     |
| Fall time   | t <sub>f</sub>                       |  | -   | 12      | 24      |       |     |
| <b>Drain-Source Body Diode Characteristics</b>                  |                                      |  |   |         |         |       |     |
| Continuous source-drain diode current                           | I <sub>S</sub>                       | T <sub>C</sub> = 25 °C   | -   | -       | 100     | A     |     |
| Pulse diode forward current                                     | I <sub>SM</sub>                      |  | -   | -       | 300     |       |     |
| Body diode voltage  | V <sub>SD</sub>                      | I <sub>S</sub> = 5 A, V <sub>GS</sub> = 0 V  | -   | 0.7     | 1.1     | V     |     |
| Body diode reverse recovery time                                | t <sub>rr</sub>                      | I <sub>F</sub> = 20 A, di/dt = 100 A/μs,<br>T <sub>J</sub> = 25 °C   | -   | 52      | 104     | ns    |     |
| Body diode reverse recovery charge                              | Q <sub>rr</sub>                      |  | -   | 50      | 100     | nC    |     |
| Reverse recovery fall time                                      | t <sub>a</sub>                       |  | -   | 25      | -       | ns    |     |
| Reverse recovery rise time                                      | t <sub>b</sub>                       |  | -   | 27      | -       |       |     |

**Notes**

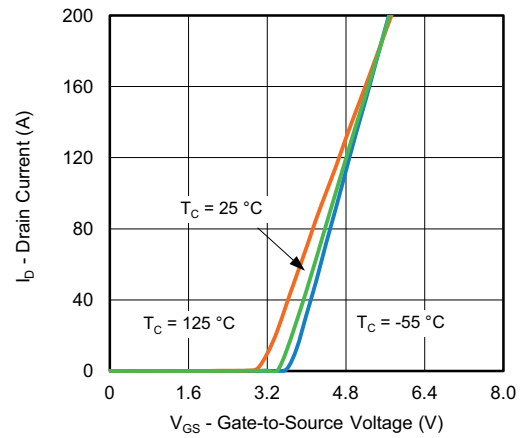
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

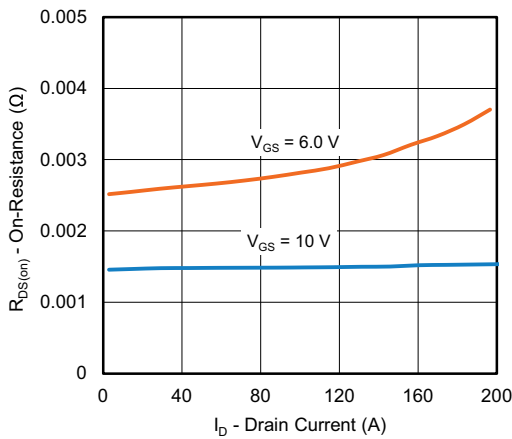
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



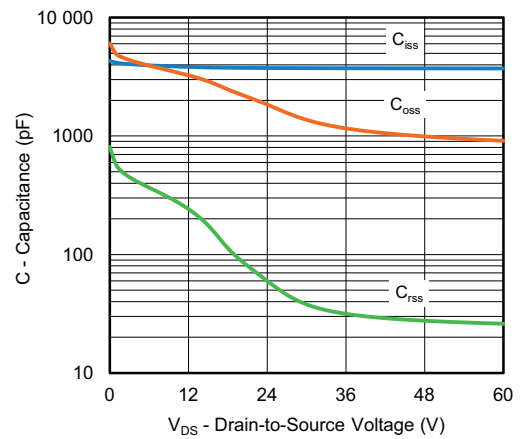
**Output Characteristics**



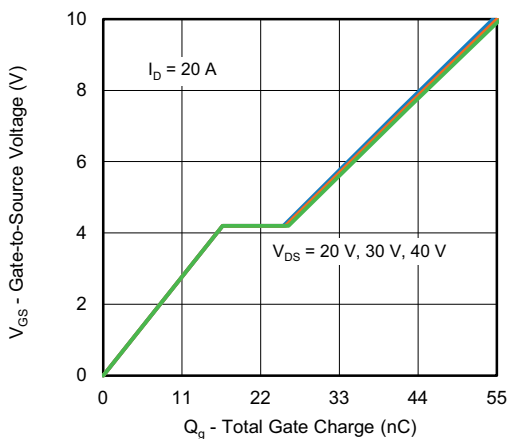
**Transfer Characteristics**



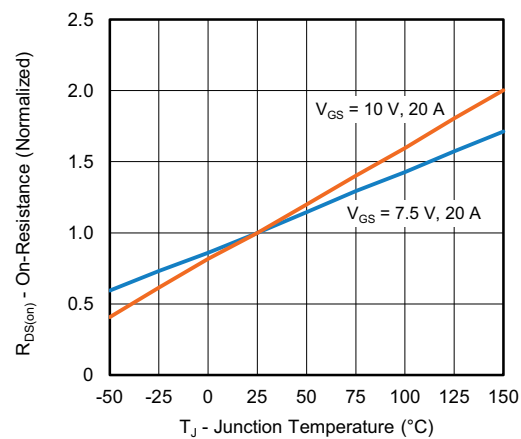
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



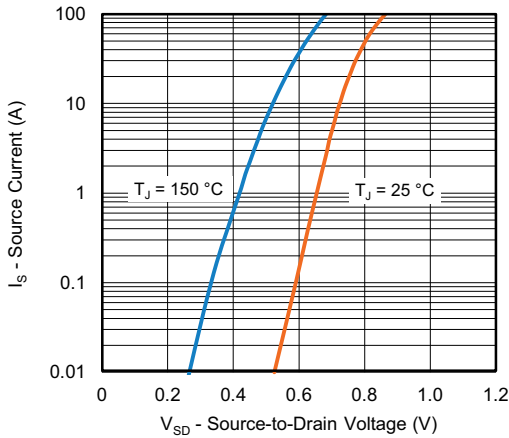
**Gate Charge**



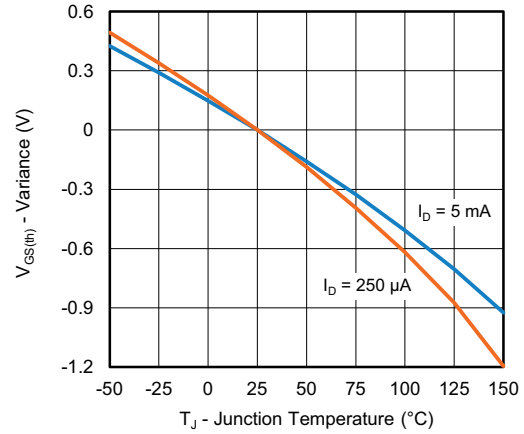
**On-Resistance vs. Junction Temperature**



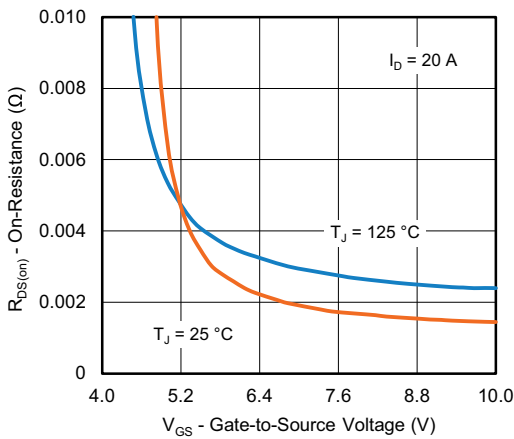
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



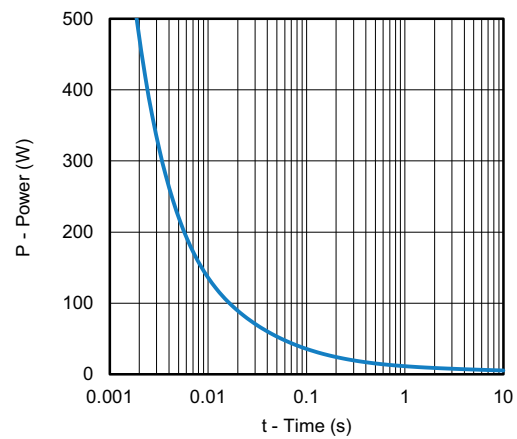
**Source-Drain Diode Forward Voltage**



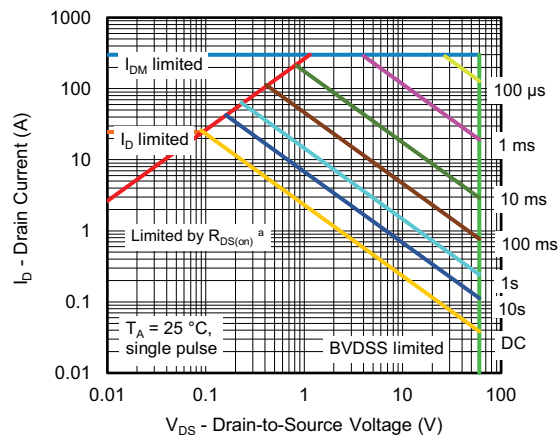
**Threshold Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**Single Pulse Power, Junction-to-Ambient**



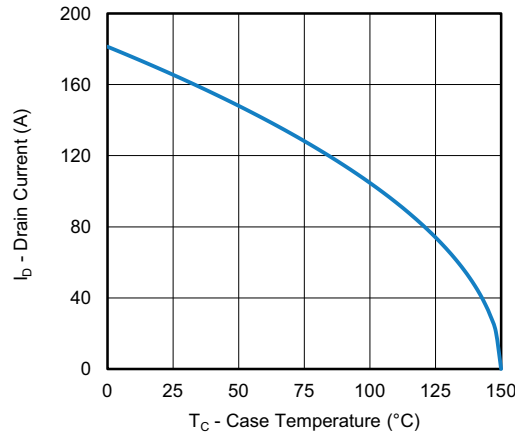
**Safe Operating Area, Junction-to-Ambient**

**Note**

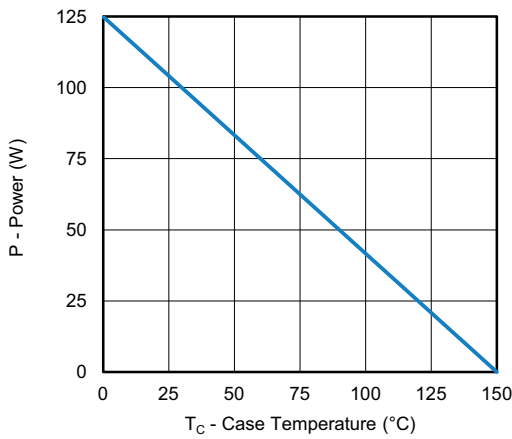
a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



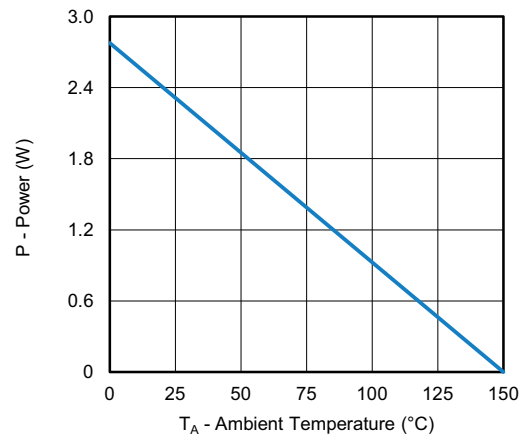
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating <sup>a</sup>



Power, Junction-to-Case



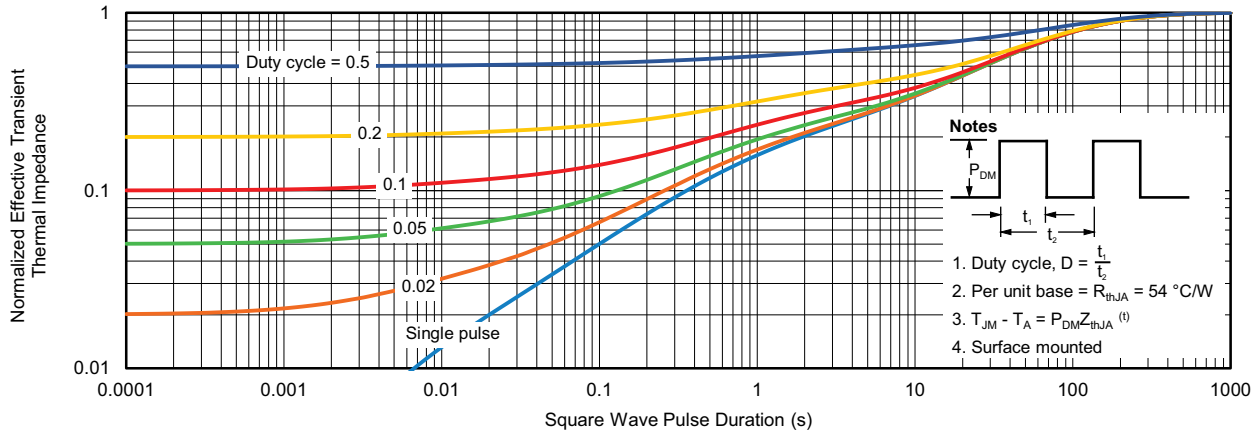
Power, Junction-to-Ambient

Note

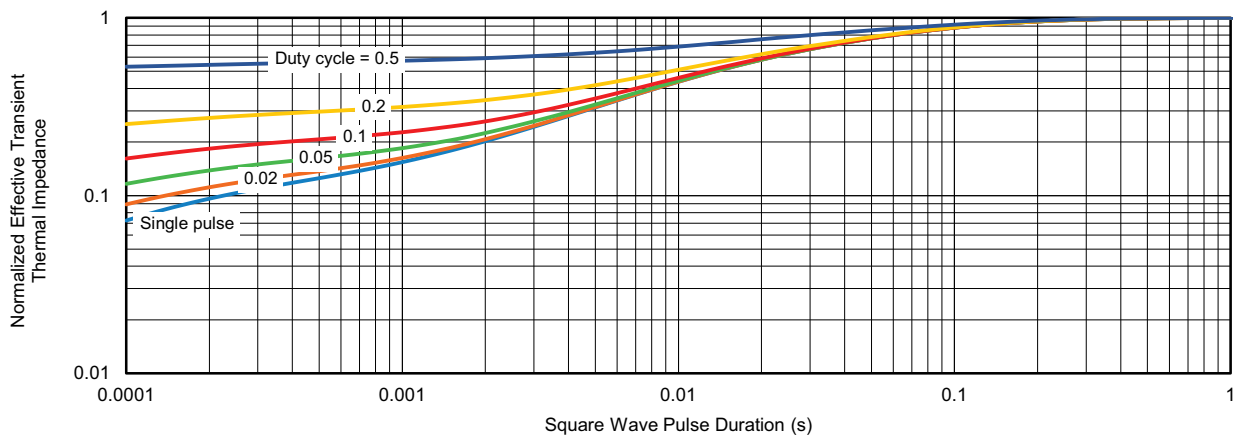
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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# PowerPAK<sup>®</sup> SO-8, (Single/Dual)



- Notes**
1. Inch will govern.
  2. Dimensions exclusive of mold gate burrs.
  3. Dimensions exclusive of mold flash and cutting burrs.

| DIM. | MILLIMETERS |      |      | INCHES      |       |       |
|------|-------------|------|------|-------------|-------|-------|
|      | MIN.        | NOM. | MAX. | MIN.        | NOM.  | MAX.  |
| A    | 0.97        | 1.04 | 1.12 | 0.038       | 0.041 | 0.044 |
| A1   |             | -    | 0.05 | 0           | -     | 0.002 |
| b    | 0.33        | 0.41 | 0.51 | 0.013       | 0.016 | 0.020 |
| c    | 0.23        | 0.28 | 0.33 | 0.009       | 0.011 | 0.013 |
| D    | 5.05        | 5.15 | 5.26 | 0.199       | 0.203 | 0.207 |
| D1   | 4.80        | 4.90 | 5.00 | 0.189       | 0.193 | 0.197 |
| D2   | 3.56        | 3.76 | 3.91 | 0.140       | 0.148 | 0.154 |
| D3   | 1.32        | 1.50 | 1.68 | 0.052       | 0.059 | 0.066 |
| D4   | 0.57 typ.   |      |      | 0.0225 typ. |       |       |
| D5   | 3.98 typ.   |      |      | 0.157 typ.  |       |       |
| E    | 6.05        | 6.15 | 6.25 | 0.238       | 0.242 | 0.246 |
| E1   | 5.79        | 5.89 | 5.99 | 0.228       | 0.232 | 0.236 |
| E2   | 3.48        | 3.66 | 3.84 | 0.137       | 0.144 | 0.151 |
| E3   | 3.68        | 3.78 | 3.91 | 0.145       | 0.149 | 0.154 |
| E4   | 0.75 typ.   |      |      | 0.030 typ.  |       |       |
| e    | 1.27 BSC    |      |      | 0.050 BSC   |       |       |
| K    | 1.27 typ.   |      |      | 0.050 typ.  |       |       |
| K1   | 0.56        | -    | -    | 0.022       | -     | -     |
| H    | 0.51        | 0.61 | 0.71 | 0.020       | 0.024 | 0.028 |
| L    | 0.51        | 0.61 | 0.71 | 0.020       | 0.024 | 0.028 |
| L1   | 0.06        | 0.13 | 0.20 | 0.002       | 0.005 | 0.008 |
| θ    | 0°          | -    | 12°  | 0°          | -     | 12°   |
| W    | 0.15        | 0.25 | 0.36 | 0.006       | 0.010 | 0.014 |
| M    | 0.125 typ.  |      |      | 0.005 typ.  |       |       |

ECN: S17-0173-Rev. L, 13-Feb-17  
DWG: 5881

## RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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